

MITSUBISHI LSIs

M5M44260CJ, TP-5, -6, -7, -5S, -6S, -7S

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

DESCRIPTION

This is a family of 262144-word by 16-bit dynamic RAMs, fabricated with the high performance CMOS process, and is ideal for memory systems where high speed, low power dissipation, and low costs are essential.

The use of double-layer metalization process technology and a single-transistor dynamic storage stacked capacitor cell provide high circuit density at reduced costs. Multiplexed address inputs permit both a reduction in pins and an increase in system densities. Self or extended refresh current is small enough for battery back-up application.

This device has 2 $\overline{\text{CAS}}$ and 1 $\overline{\text{W}}$ terminals with a refresh cycle of 512 cycles every 8.2ms.

FEATURES

Type name	$\overline{\text{RAS}}$ access time (max.ns)	$\overline{\text{CAS}}$ access time (max.ns)	Address access time (max.ns)	$\overline{\text{OE}}$ access time (max.ns)	Cycle time (min.ns)	Power dissipation (typ.mW)
M5M44260CXX-5,-5S	50	13	25	13	90	625
M5M44260CXX-6,-6S	60	15	30	15	110	550
M5M44260CXX-7,-7S	70	20	35	20	130	475

XX=J,TP

- Standard 40pin SOJ, 44 pin TSOP (II)
- Single 5V±10% supply
- Low stand-by power dissipation
 - CMOS Input level ----- 5.5mW (Max)
 - CMOS Input level ----- 550μW (Max) *
- Operating power dissipation
 - M5M44260Cxx-5,-5S ----- 688mW (Max)
 - M5M44260Cxx-6,-6S ----- 605mW (Max)
 - M5M44260Cxx-7,-7S ----- 523mW (Max)
- Self refresh capability *
 - Self refresh current ----- 150μA (Max)
- Extended refresh capability
 - Extended refresh current ----- 150μA (Max)
- Fast-page mode (512-column random access), Read-modify-write, $\overline{\text{RAS}}$ -only refresh, $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh, Hidden refresh capabilities.
- Early-write mode, $\overline{\text{LCAS}}$ / $\overline{\text{UCAS}}$ and $\overline{\text{OE}}$ to control output buffer impedance
- 512 refresh cycles every 8.2ms (A₀~A₈)
- 512 refresh cycles every 128ms (A₀~A₈) *
- Byte or word control for Read/Write operation (2 $\overline{\text{CAS}}$, 1 $\overline{\text{W}}$ type)
 - * : Applicable to self refresh version (M5M44260CJ, TP-5S, -6S, -7S : option) only

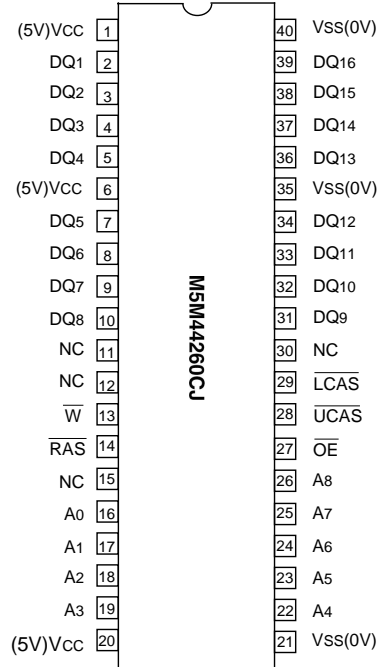
APPLICATION

Microcomputer memory, Refresh memory for CRT

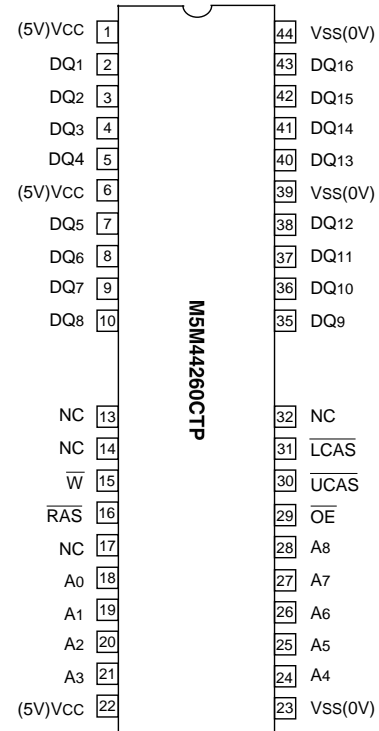
PIN DESCRIPTION

Pin name	Function
A ₀ ~A ₈	Address inputs
DQ ₁ ~DQ ₁₆	Data inputs / outputs
$\overline{\text{RAS}}$	Row address strobe input
$\overline{\text{LCAS}}$	Lower byte control column address strobe input
$\overline{\text{UCAS}}$	Upper byte control column address strobe input
$\overline{\text{W}}$	Write control input
$\overline{\text{OE}}$	Output enable input
V _{cc}	Power supply (+5V)
V _{ss}	Ground (0V)

PIN CONFIGURATION (TOP VIEW)



Outline 40P0K (400mil SOJ)



Outline 44P3W-R (400mil TSOP Nomal Bend)

NC: NO CONNECTION

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FUNCTION

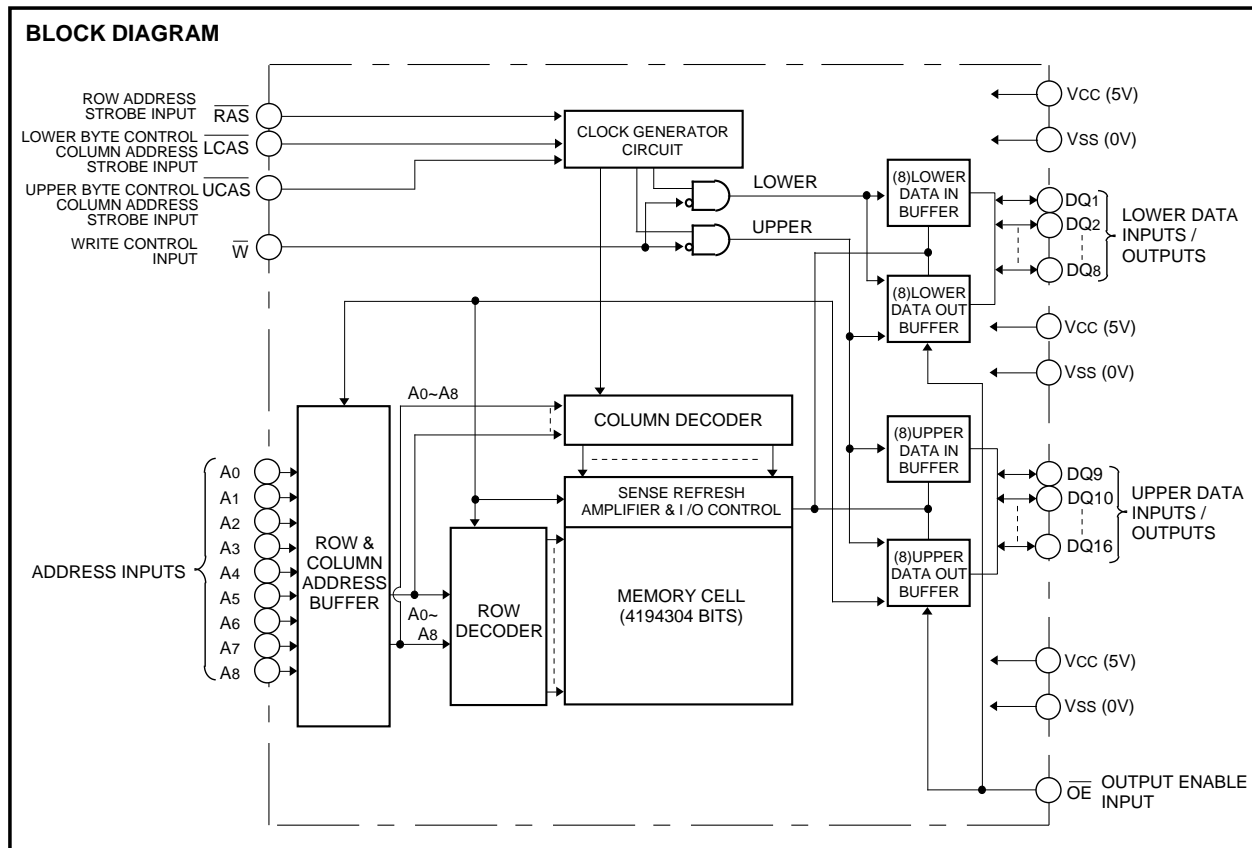
In addition to normal read, write and read-modify-write operations the M5M44260CJ, TP provides a number of other functions, e.g.,

fast page mode, $\overline{\text{RAS}}$ -only refresh and delayed-write. The input conditions for each are shown in Table 1.

Table 1 Input conditions for each mode

Operation	Inputs						Input/Output		Refresh	Remark	
	$\overline{\text{RAS}}$	$\overline{\text{LCAS}}$	$\overline{\text{UCAS}}$	$\overline{\text{W}}$	$\overline{\text{OE}}$	Row address	Column address	DQ1~DQ8			DQ9~DQ16
Lower byte read	ACT	ACT	NAC	NAC	ACT	APD	APD	DOUT	OPN	YES	Fast page mode identical
Upper byte read	ACT	NAC	ACT	NAC	ACT	APD	APD	OPN	DOUT	YES	
Word read	ACT	ACT	ACT	NAC	ACT	APD	APD	DOUT	DOUT	YES	
Lower byte write	ACT	ACT	NAC	ACT	NAC	APD	APD	DIN	DNC	YES	
Upper byte write	ACT	NAC	ACT	ACT	NAC	APD	APD	DNC	DIN	YES	
Word write	ACT	ACT	ACT	ACT	NAC	APD	APD	DIN	DIN	YES	
$\overline{\text{RAS}}$ only refresh	ACT	NAC	NAC	DNC	DNC	APD	DNC	OPN	OPN	YES	
Hidden refresh	ACT	ACT	ACT	DNC	ACT	DNC	DNC	DOUT	DOUT	YES	
CAS before $\overline{\text{RAS}}$ (Extended *) refresh	ACT	ACT	ACT	DNC	DNC	DNC	DNC	OPN	OPN	YES	
Self refresh *	ACT	ACT	ACT	DNC	DNC	DNC	DNC	OPN	OPN	YES	
Stand-by	NAC	DNC	DNC	DNC	DNC	DNC	DNC	OPN	OPN	No	

Note : ACT : active, NAC : nonactive, DNC : don't care, OPN : open



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ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Conditions	Ratings	Unit
V _{CC}	Supply voltage	With respect to V _{SS}	-1~7	V
V _I	Input voltage		-1~7	V
V _O	Output voltage		-1~7	V
I _O	Output current		50	mA
P _d	Power dissipation	T _a =25°C	1000	mW
T _{opr}	Operating temperature		0~70	°C
T _{stg}	Storage temperature		-65~150	°C

RECOMMENDED OPERATING CONDITIONS (T_a=0~70°C, unless otherwise noted) (Note 1)

Symbol	Parameter	Limits			Unit
		Min	Nom	Max	
V _{CC}	Supply voltage	4.5	5.0	5.5	V
V _{SS}	Supply voltage	0	0	0	V
V _{IH}	High-level input voltage, all inputs	2.4		6.0	V
V _{IL}	Low-level input voltage, all inputs	-0.5 **		0.8	V

Note 1 : All voltage values are with respect to V_{SS}.

** : V_{IL}(min) is -2.0V when pulse width is less than 25ns. (Pulse width is with respect to V_{SS}.)

ELECTRICAL CHARACTERISTICS (T_a=0~70°C, V_{CC}=5V±10%, V_{SS}=0V, unless otherwise noted) (Note 2)

Symbol	Parameter	Test conditions	Limits			Unit	
			Min	Typ	Max		
V _{OH}	High-level output voltage	I _{OH} =-5mA	2.4		V _{CC}	V	
V _{OL}	Low-level output voltage	I _{OL} =4.2mA	0		0.4	V	
I _{OZ}	Off-state output current	Q floating 0V V _{OUT} 5.5V	-10		10	µA	
I _I	Input current	0V V _{IN} +6.0V, Other inputs pins=0V	-10		10	µA	
I _{CC1} (AV)	Average supply current from V _{CC} , operating (Note 3,4,5)	M5M44260C-5,-5S	RAS, CAS cycling trc=twc=min. output open			125	mA
		M5M44260C-6,-6S				110	
		M5M44260C-7,-7S				95	
I _{CC2}	Supply current from V _{CC} , stand-by (Note 6)	RAS= CAS =V _{IH} , output open				2	mA
		RAS= CAS V _{CC} -0.5V output open				1.0	
						0.1 *	
I _{CC3} (AV)	Average supply current from V _{CC} , RAS only refresh mode (Note 3,5)	M5M44260C-5,-5S	RAS cycling, CAS=V _{IH} trc=min. output open			125	mA
		M5M44260C-6,-6S				110	
		M5M44260C-7,-7S				95	
I _{CC4} (AV)	Average supply current from V _{CC} Fast page mode (Note 3,4,5)	M5M44260C-5,-5S	RAS=V _{IL} , CAS cycling tpc=min. output open			125	mA
		M5M44260C-6,-6S				110	
		M5M44260C-7,-7S				95	
I _{CC6} (AV)	Average supply current from V _{CC} CAS before RAS refresh cycling mode (Note 3,5)	M5M44260C-5,-5S	CAS before RAS refresh cycling trc=min. output open			115	mA
		M5M44260C-6,-6S				100	
		M5M44260C-7,-7S				85	
I _{CC8} (AV) *	Average supply current from V _{CC} Extended-refresh mode (Note 6)	RAS cycling CAS 0.2V or CAS before RAS refresh cycling RAS 0.2V or V _{CC} -0.2V CAS 0.2V or V _{CC} -0.2V W 0.2V or V _{CC} -0.2V OE 0.2V or V _{CC} -0.2V A ₀ -A ₈ 0.2V or V _{CC} -0.2V, DQ=open trc=250µs, trAS=trAS min~1µs				150	µA
I _{CC9} (AV) *	Average supply current from V _{CC} Self-refresh mode (Note 6)	RAS=CAS 0.2V output open				150	µA

Note 2: Current flowing into an IC is positive, out is negative.

3: I_{CC1} (AV), I_{CC3} (AV), I_{CC4} (AV), and I_{CC6} (AV) are dependent on cycle rate. Maximum current is measured at the fastest cycle rate.

4: I_{CC1} (AV) and I_{CC4} (AV) are dependent on output loading. Specified values are obtained with the output open.

5: Column Address can be changed once or less while RAS=V_{IL} and CAS=V_{IH}.

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CAPACITANCE (Ta=0~70°C, Vcc=5V±10%, Vss=0V, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min	Typ	Max	
CI(A)	Input capacitance, address inputs	Vi=Vss f=1MHz Vi=25mVrms			5	pF
CI(CLK)	Input capacitance, clock inputs				7	pF
CI/O	Input/Output capacitance, data ports				7	pF

SWITCHING CHARACTERISTICS (Ta=0~70°C, Vcc=5V±10%, Vss=0V, unless otherwise noted, see notes 6,13,14)

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
tCAC	Access time from $\overline{\text{CAS}}$ (Note 7,8)		13		15		20	ns
tRAC	Access time from $\overline{\text{RAS}}$ (Note 7,9)		50		60		70	ns
tAA	Column address access time (Note 7,10)		25		30		35	ns
tCPA	Access time from $\overline{\text{CAS}}$ precharge (Note 7,11)		30		35		40	ns
tOEA	Access time from $\overline{\text{OE}}$ (Note 7)		13		15		20	ns
tCLZ	Output low impedance time from $\overline{\text{CAS}}$ low (Note 7)	5		5		5		ns
tOFF	Output disable time after $\overline{\text{CAS}}$ high (Note 12)		13		15		20	ns
tOEZ	Output disable time after $\overline{\text{OE}}$ high (Note 12)		13		15		20	ns

Note 6: An initial pause of 500 μs is required after power-up followed by a minimum of eight initialization cycles ($\overline{\text{RAS}}$ -only refresh or $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh cycles).

Note the $\overline{\text{RAS}}$ may be cycled during the initial pause. And 8 initialization cycles are required after prolonged periods (greater than 8.2ms) of $\overline{\text{RAS}}$ inactivity before proper device operation is achieved.

7: Measured with a load circuit equivalent to 2TTL loads and 100pF.

8: Assumes that tRCD = tRCD(max) and tASC = tASC(max).

9: Assumes that tRCD = tRCD(max) and tRAD = tRAD(max). If tRCD or tRAD is greater than the maximum recommended value shown in this table, tRAC will increase by amount that tRCD exceeds the value shown.

10: Assumes that tRAD = tRAD(max) and tASC = tASC(max).

11: Assumes that tCP = tCP(max) and tASC = tASC(max).

12: tOFF(max) and tOEZ(max) defines the time at which the output achieves the high impedance state (IOUT = ±10 μA) and is not reference to VOH(min) or VOL(max).

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TIMING REQUIREMENTS (For Read, Write, Read-Modify-Write, Refresh and Fast-Page Mode Cycles)

(Ta=0~70°C, Vcc=5V±10%, Vss=0V, unless otherwise noted, see notes 6,13,14)

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
tREF	Refresh cycle time		8.2		8.2		8.2	ms
tREF	Refresh cycle time *		128		128		128	ms
tRP	RAS high pulse width	30		40		50		ns
tRCD	Delay time, RAS low to CAS low (Note 15)	18	37	20	45	20	50	ns
tCRP	Delay time, CAS high to RAS low	5		5		5		ns
tRPC	Delay time, RAS high to CAS low	0		0		0		ns
tCPN	CAS high pulse width	10		10		10		ns
tRAD	Column address delay time from RAS low (Note 16)	13	25	15	30	15	35	ns
tASR	Row address setup time before RAS low	0		0		0		ns
tASC	Column address setup time before CAS low (Note 17)	0	7	0	10	0	10	ns
tRAH	Row address hold time after RAS low	8		10		10		ns
tCAH	Column address hold time after CAS low	13		15		15		ns
tDZC	Delay time, data to CAS low (Note 18)	0		0		0		ns
tDZO	Delay time, data to OE low (Note 18)	0		0		0		ns
tCDD	Delay time, CAS high to data (Note 19)	13		15		20		ns
tODD	Delay time, OE high to data (Note 19)	13		15		20		ns
tT	Transition time (Note 20)	1	50	1	50	1	50	ns

Note 13: The timing requirements are assumed tT =5ns.

14: VIH(min) and VIL(max) are reference levels for measuring timing of input signals.

15: tRCD(max) is specified as a reference point only. If tRCD is less than tRCD(max), access time is tRAC. If tRCD is greater than tRCD(max), access time is controlled exclusively by tCAC or tAA.

16: tRAD(max) is specified as a reference point only. If tRAD tRAD(max) and tASC tASC(max), access time is controlled exclusively by tAA.

17: tASC(max) is specified as a reference point only. If tRCD tRCD(max) and tASC tASC(max), access time is controlled exclusively by tCAC.

18: Either tDZC or tDZO must be satisfied.

19: Either tCDD or tODD must be satisfied.

20: tT is measured between VIH(min) and VIL(max).

Read and Refresh Cycles

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
tRC	Read cycle time	90		110		130		ns
tRAS	RAS low pulse width	50	10000	60	10000	70	10000	ns
tCAS	CAS low pulse width	13	10000	15	10000	20	10000	ns
tCSH	CAS hold time after RAS low	50		60		70		ns
tRSH	RAS hold time after CAS low	13		15		20		ns
tRCS	Read setup time before CAS low	0		0		0		ns
tRCH	Read hold time after CAS high (Note 21)	0		0		0		ns
tRRH	Read hold time after RAS high (Note 21)	0		0		0		ns
tRAL	Column address to RAS hold time	25		30		35		ns
tOCH	CAS hold time after OE low	13		15		20		ns
tORH	RAS hold time after OE low	13		15		20		ns

Note 21: Either tRCH or tRRH must be satisfied for a read cycle.

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Write Cycle (Early Write and Delayed Write)

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
tWC	Write cycle time	90		110		130		ns
tRAS	RAS low pulse width	50	10000	60	10000	70	10000	ns
tCAS	CAS low pulse width	13	10000	15	10000	20	10000	ns
tCSH	CAS hold time after RAS low	50		60		70		ns
trSH	RAS hold time after CAS low	13		15		20		ns
twCS	Write setup time before CAS low (Note 23)	0		0		0		ns
twCH	Write hold time after CAS low	8		10		15		ns
tcWL	CAS hold time after W low	13		15		20		ns
trWL	RAS hold time after W low	13		15		20		ns
tWP	Write pulse width	8		10		15		ns
tDS	Data setup time before CAS low or W low	0		0		0		ns
tDH	Data hold time after CAS low or W low	8		10		15		ns
toEH	OE hold time after W low	13		15		20		ns

Read-Write and Read-Modify-Write Cycles

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
trWC	Read write/read modify write cycle time (Note 22)	126		150		180		ns
tRAS	RAS low pulse width	86	10000	100	10000	120	10000	ns
tCAS	CAS low pulse width	49	10000	55	10000	70	10000	ns
tCSH	CAS hold time after RAS low	86		100		120		ns
trSH	RAS hold time after CAS low	49		55		70		ns
trCS	Read setup time before CAS low	0		0		0		ns
tcWD	Delay time, CAS low to W low (Note 23)	31		35		45		ns
trWD	Delay time, RAS low to W low (Note 23)	68		80		95		ns
tAWD	Delay time, address to W low (Note 23)	43		50		60		ns
tcWL	CAS hold time after W low	13		15		20		ns
trWL	RAS hold time after W low	13		15		20		ns
tWP	Write pulse width	8		10		15		ns
tDS	Data setup time before CAS low or W low	0		0		0		ns
tDH	Data hold time after CAS low or W low	8		10		15		ns
toEH	OE hold time after W low	13		15		20		ns

Note 22: trWC is specified as $trWC(min)=trAC(max)+tODD(min)+trWL(min)+trP(min)+4t$.

23: twCS, tcWD, trWD and tAWD are specified as reference points only. If twCS twCS(min) the cycle is an early write cycle and the DQ pins will remain high impedance throughout the entire cycle. If tcWD tcWD(min), trWD trWD(min), tAWD tAWD(min) and tcPWD tcPWD(min) (for fast page mode cycle only), the cycle is a read-modify-write cycle and the DQ will contain the data read from the selected address. If neither of the above condition (delayed write) of the DQ (at access time and until CAS or OE goes back to VIH) is indeterminate.

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Fast-Page Mode Cycle (Read, Early Write, Read -Write, Read-Modify-Write Cycle) (Note 24)

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
tPC	Fast page mode read/write cycle time	35		40		45		ns
tPRWC	Fast page mode read write/read modify write cycle time	71		80		95		ns
tRAS	$\overline{\text{RAS}}$ low pulse width for read or write cycle (Note 25)	85	100000	100	100000	115	100000	ns
tCP	$\overline{\text{CAS}}$ high pulse width (Note 26)	8	12	10	15	10	15	ns
tCPRH	$\overline{\text{RAS}}$ hold time after $\overline{\text{CAS}}$ precharge	30		35		40		ns
tCPWD	Delay time, $\overline{\text{CAS}}$ precharge to $\overline{\text{W}}$ low (Note 23)	48		55		65		ns

Note 24: All previously specified timing requirements and switching characteristics are applicable to their respective fast page mode cycle.

25: tRAS(min) is specified as two cycles of $\overline{\text{CAS}}$ input are performed.

26: tCP(max) is specified as a reference point only.

$\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ Refresh Cycle, Extended Refresh Cycle * (Note 27)

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
tCSR	$\overline{\text{CAS}}$ setup time before $\overline{\text{RAS}}$ low	5		5		5		ns
tCHR	$\overline{\text{CAS}}$ hold time after $\overline{\text{RAS}}$ low	10		10		15		ns
tCAS	$\overline{\text{CAS}}$ low pulse width	20		20		25		ns

Note 27: Eight or more $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ cycles instead of eight $\overline{\text{RAS}}$ cycles are necessary for proper operation of $\overline{\text{CAS}}$ before $\overline{\text{RAS}}$ refresh mode.

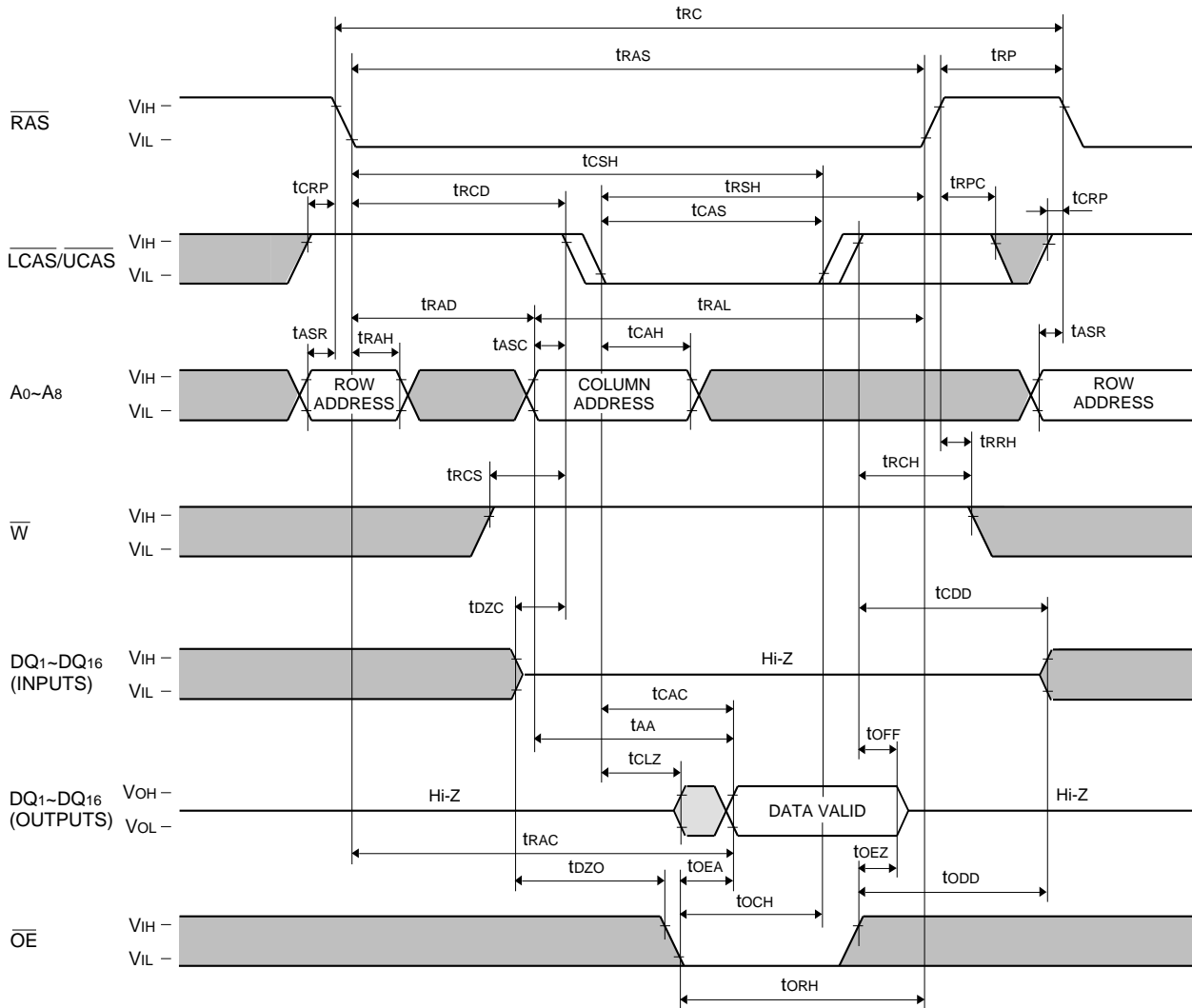
Self Refresh Cycle * (Note 28)

Symbol	Parameter	Limits						Unit
		M5M44260C-5,-5S		M5M44260C-6,-6S		M5M44260C-7,-7S		
		Min	Max	Min	Max	Min	Max	
tRASS	CBR self refresh $\overline{\text{RAS}}$ low pulse width	100		100		100		μs
tRPS	CBR self refresh $\overline{\text{RAS}}$ high precharge time	90		110		130		ns
tCHS	CBR self refresh $\overline{\text{CAS}}$ hold time	-50		-50		-50		ns

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Timing Diagrams (Note 29) Read Cycle



Note 29

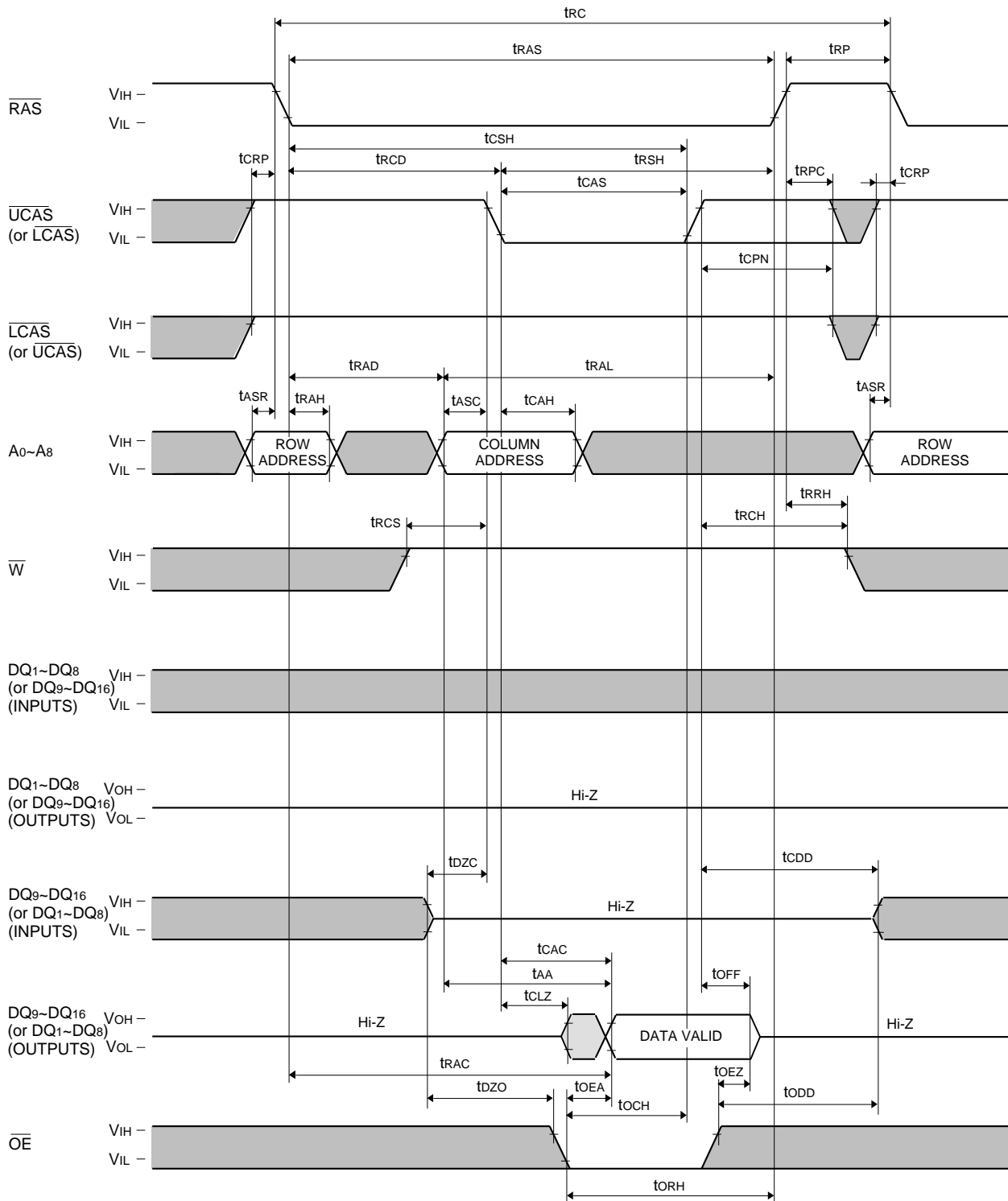


$V_{IH(min)}$ V_{IN} $V_{IH(max)}$ or $V_{IL(min)}$ V_{IN} $V_{IL(max)}$

Indicates the invalid output.

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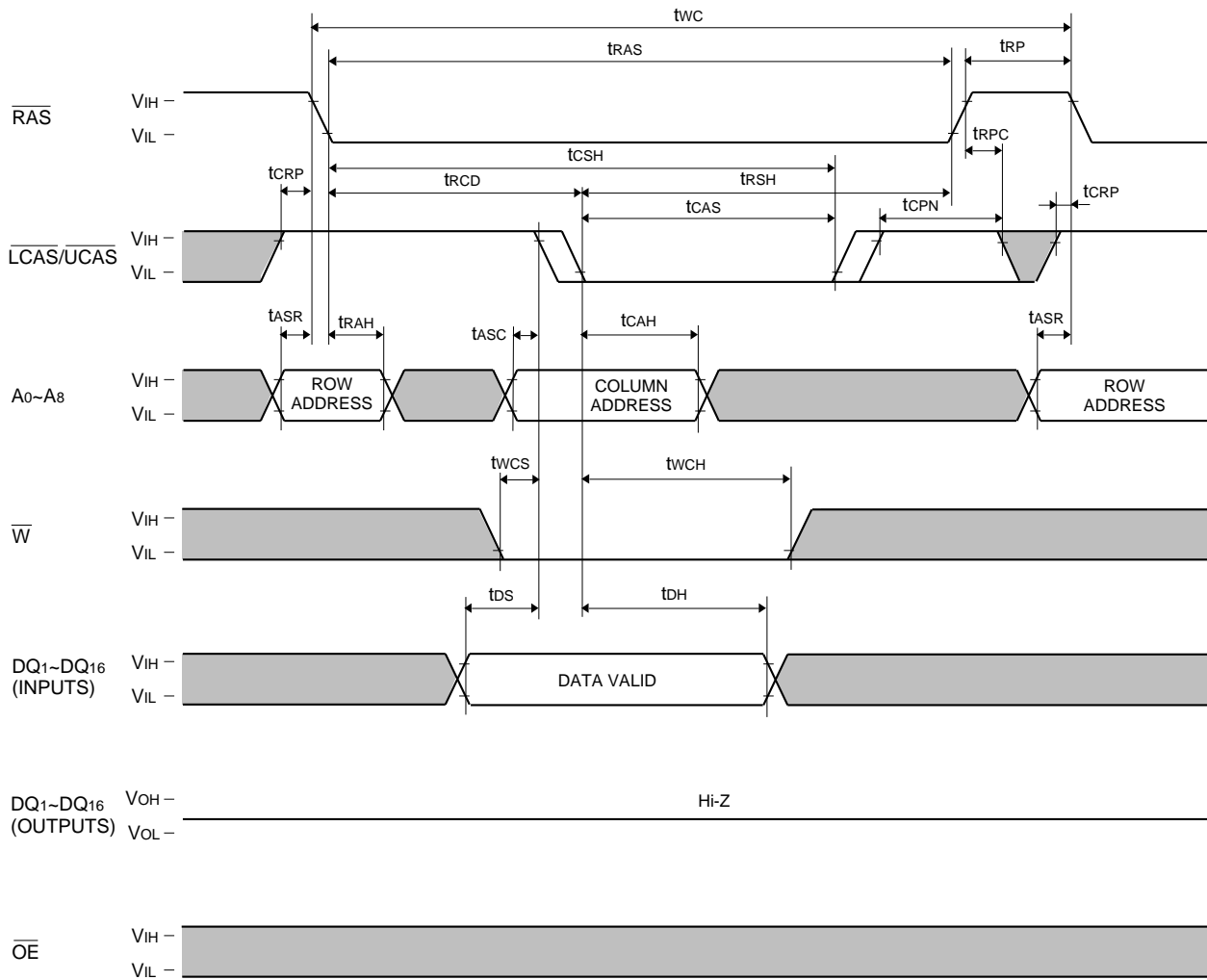
Byte Read Cycle



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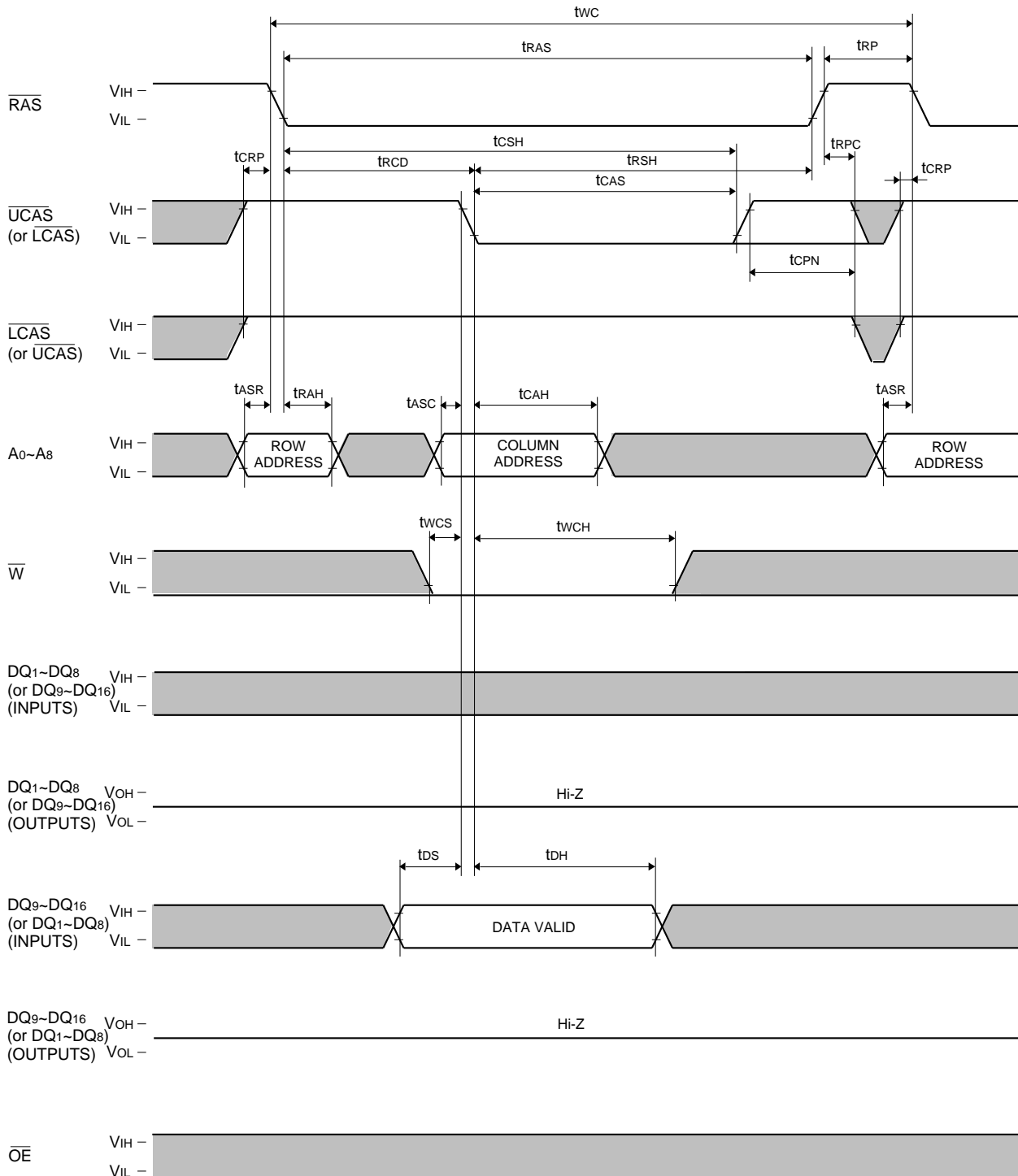
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Write Cycle (Early write)



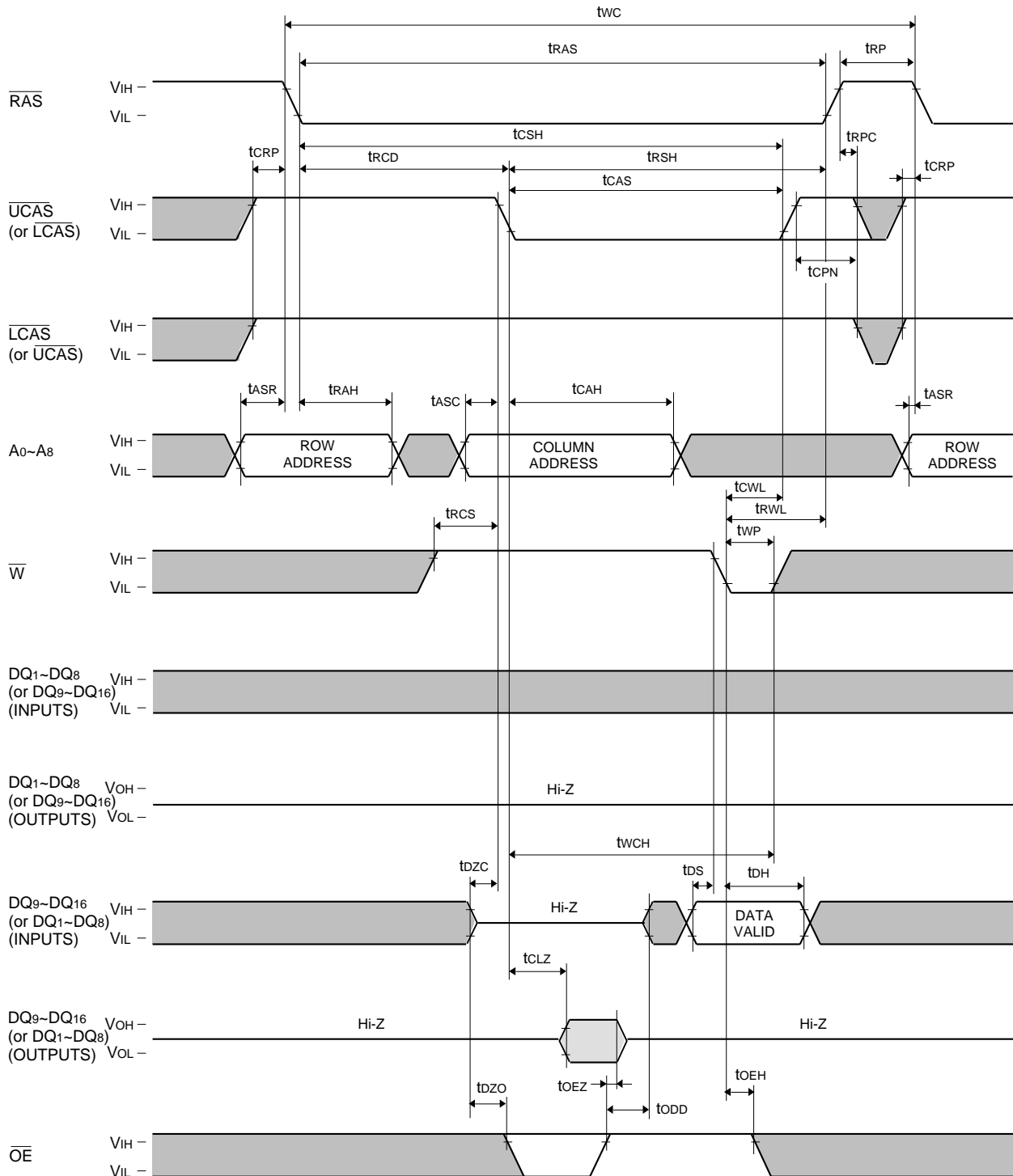
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Byte Write Cycle (Early write)



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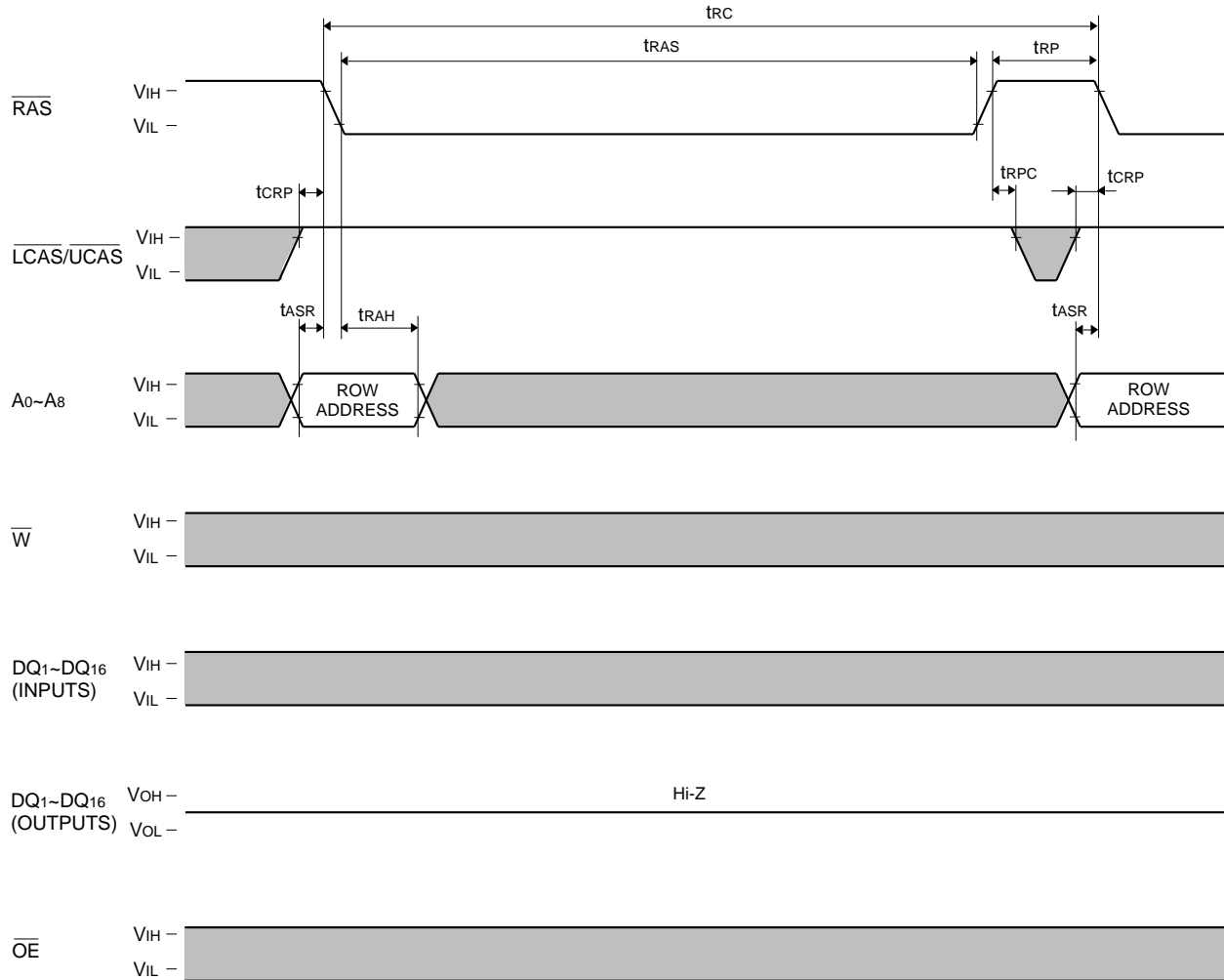
Byte Write Cycle (Delayed write)



MITSUBISHI LSIs
M5M44260CJ, TP-5, -6, -7, -5S, -6S, -7S

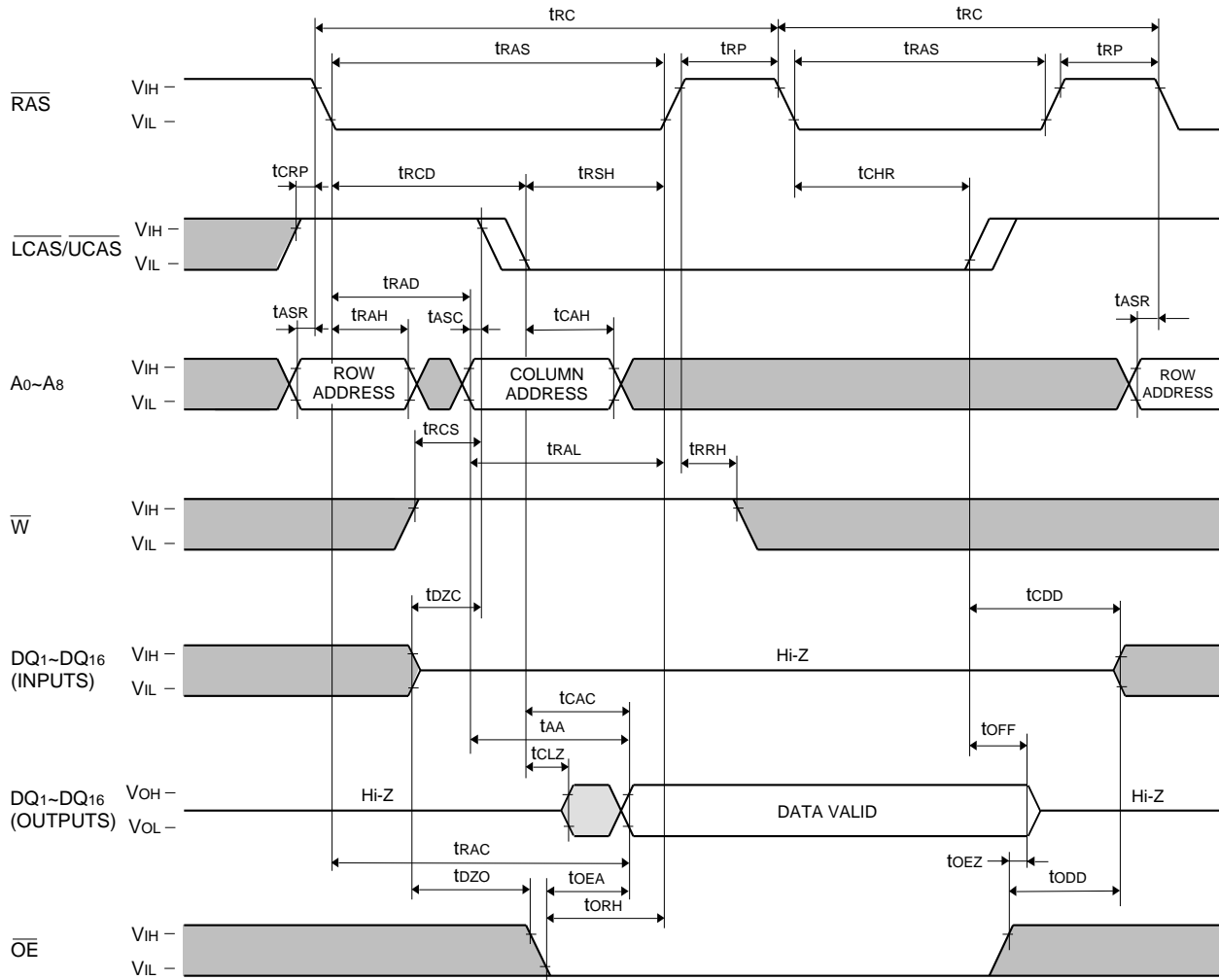
FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

RAS-only Refresh Cycle



FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

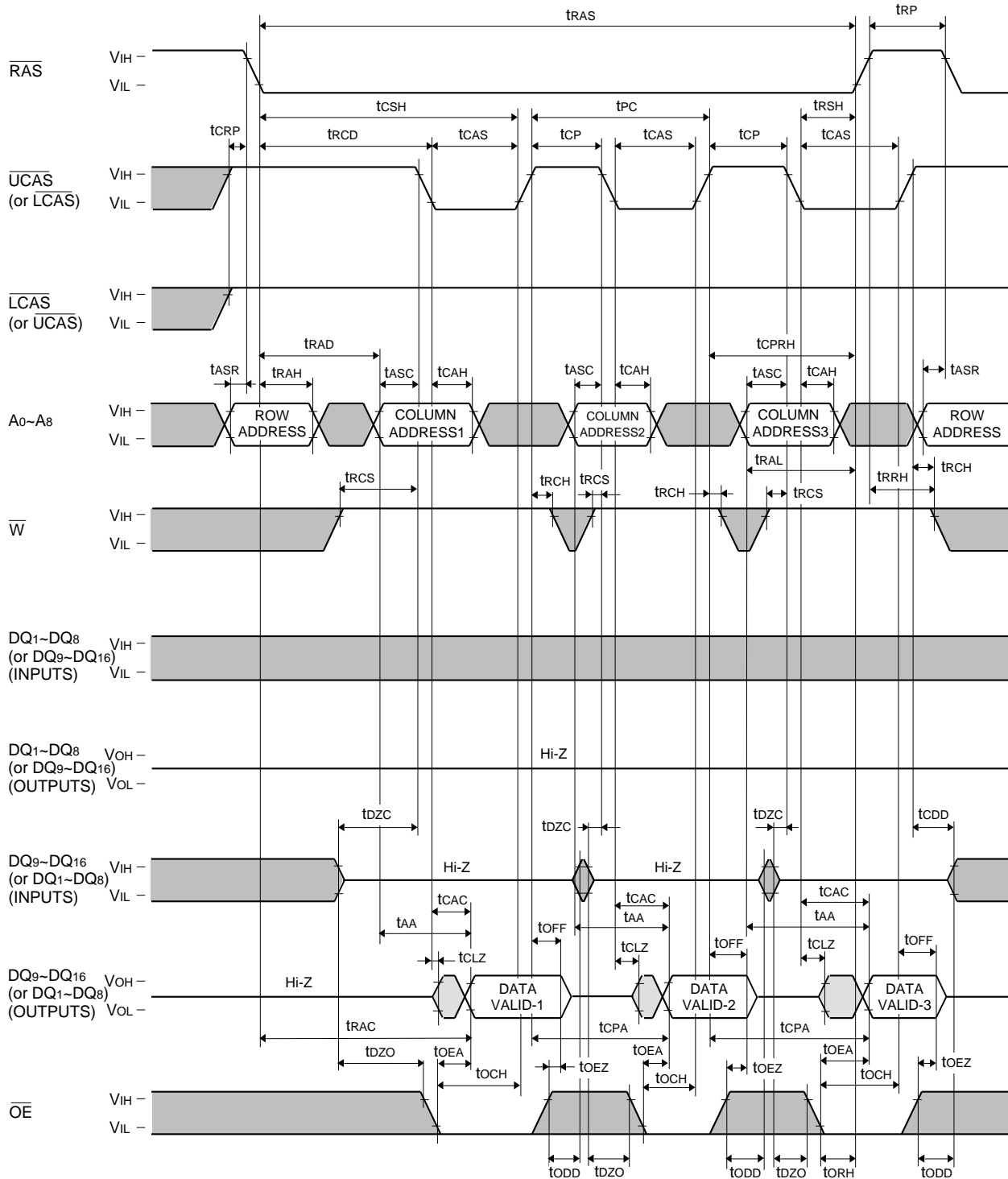
Hidden Refresh Cycle (Read) (Note 30)



Note 30: Early write, delayed write, read write or read modify write cycle is applicable instead of read cycle.
 Timing requirements and output state are the same as that of each cycle described above.

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

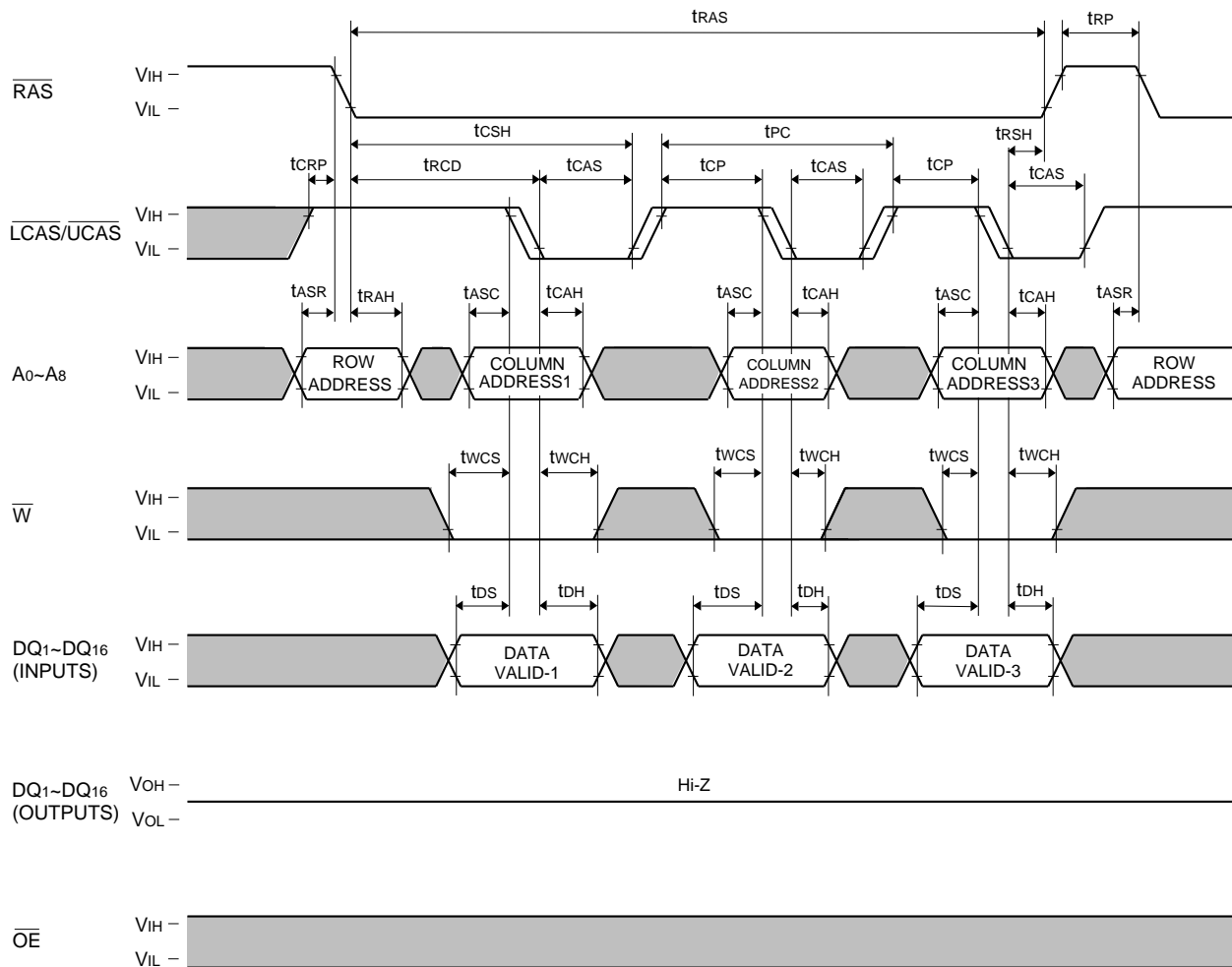
Fast Page Mode Byte Read Cycle



M5M44260CJ, TP-5, -6, -7, -5S, -6S, -7S

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

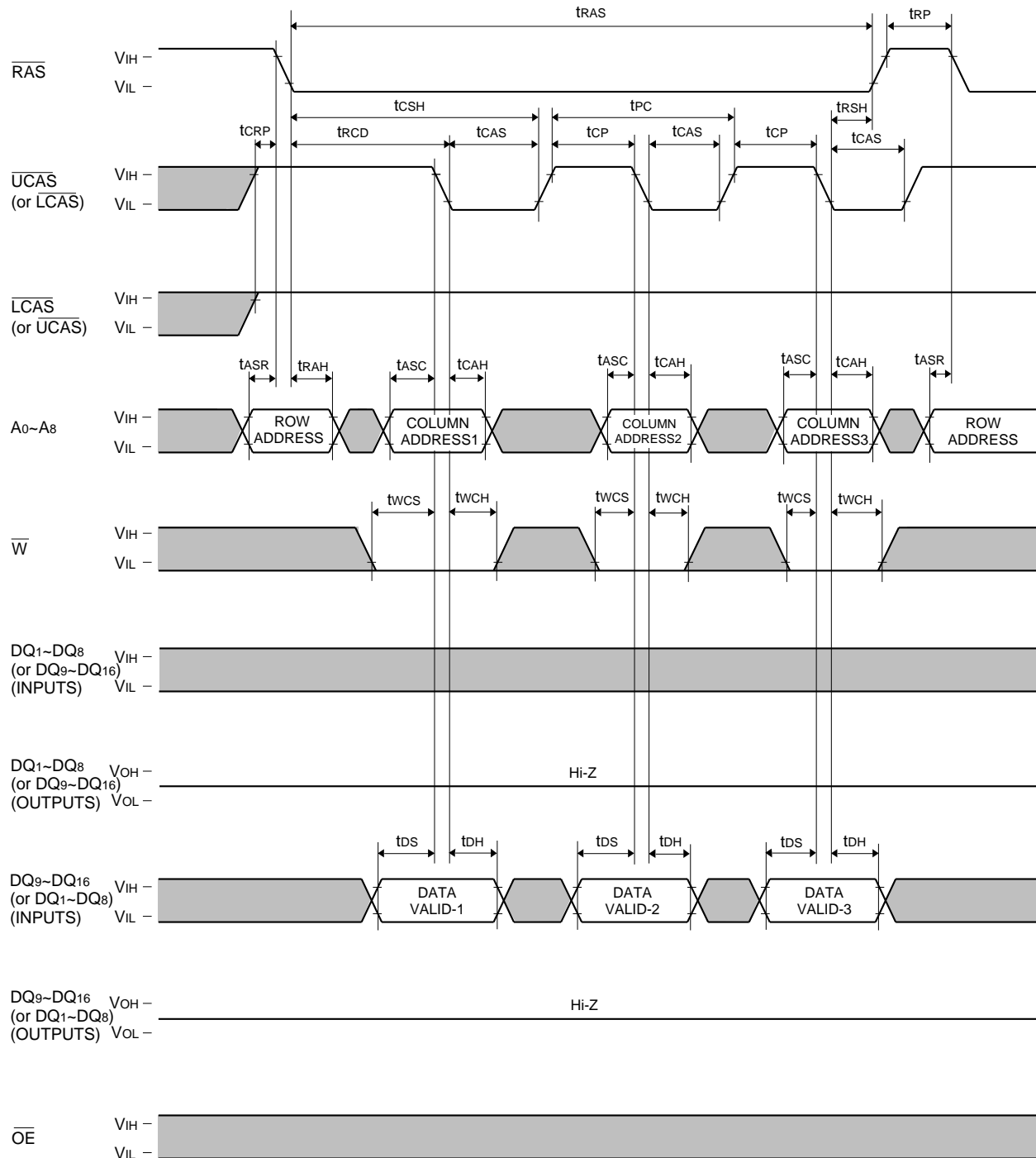
Fast Page Mode Write Cycle (Early Write)



M5M44260CJ, TP-5, -6, -7, -5S, -6S, -7S

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

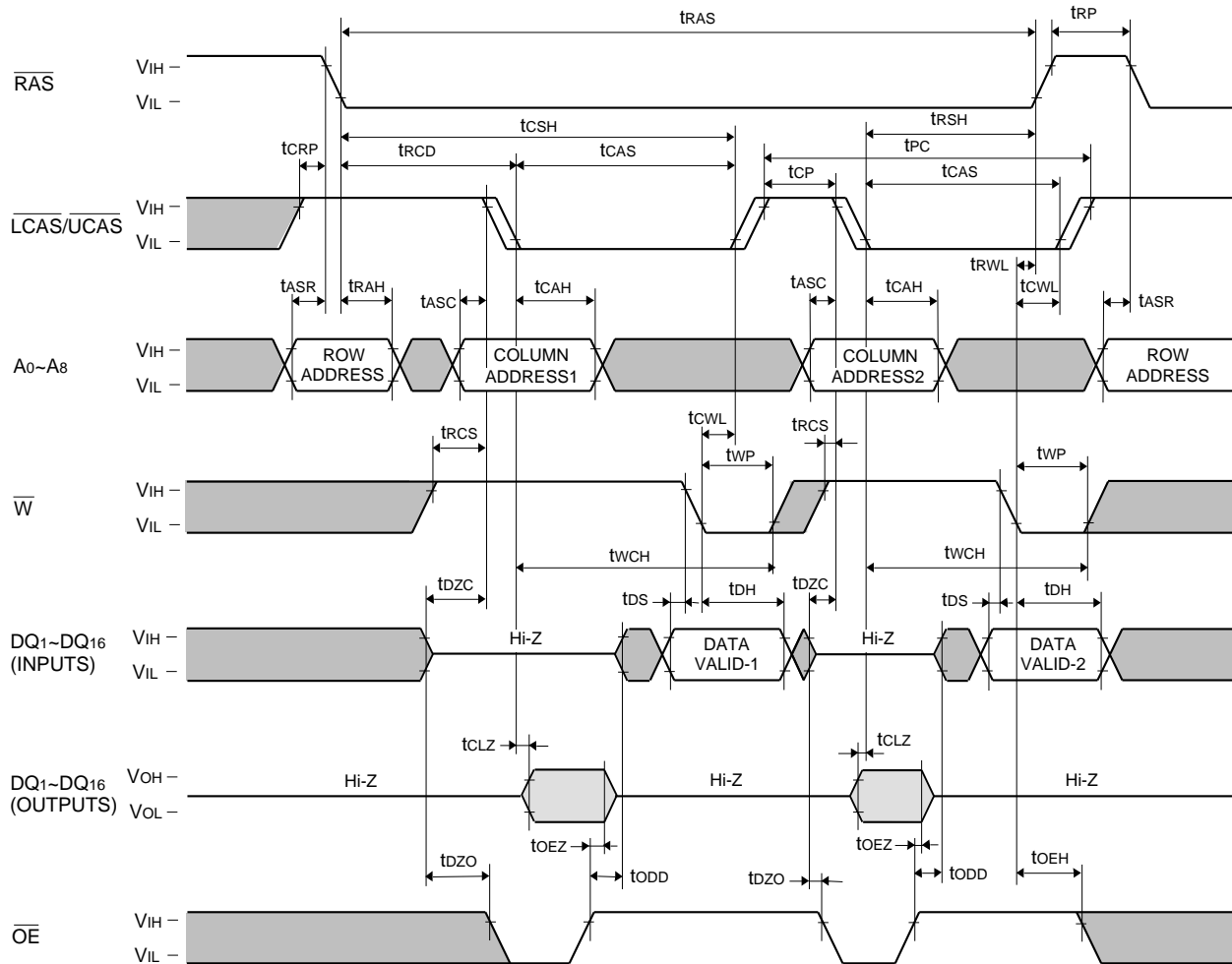
Fast Page Mode Byte Write Cycle (Early Write)



M5M44260CJ, TP-5, -6, -7, -5S, -6S, -7S

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

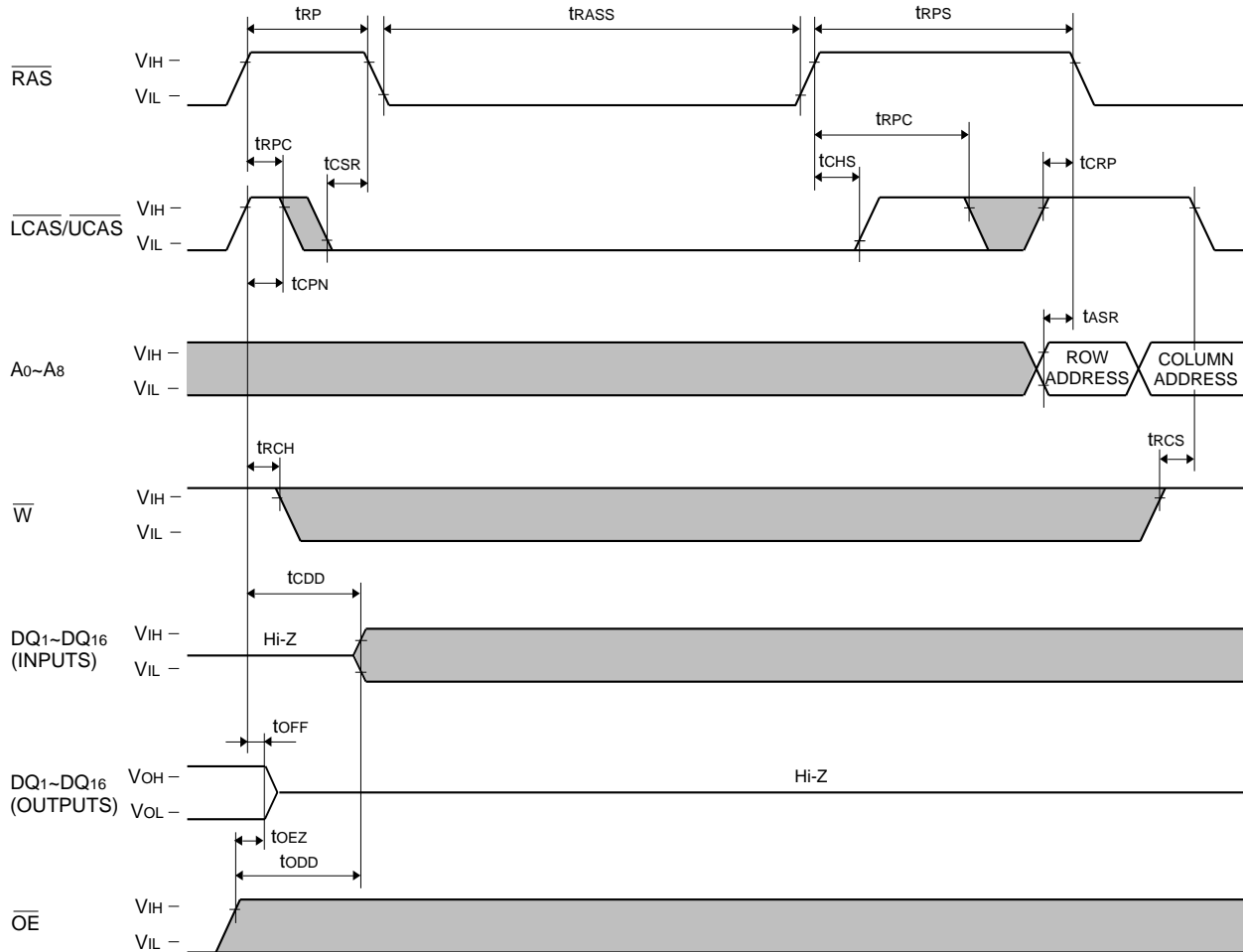
Fast-Page Mode Write Cycle (Delayed Write)



MITSUBISHI LSIs
M5M44260CJ,TP-5,-6,-7,-5S,-6S,-7S

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

Self Refresh Cycle * (Note28)



M5M44260CJ, TP-5,-6,-7,-5S,-6S,-7S

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

Note 28 : Self refresh sequence

Two refreshing methods should be used properly depending on the low pulse width (t_{RASS}) of \overline{RAS} signal during self refresh period.

1. Distributed refresh during Read/Write operation

(A) Timing Diagram

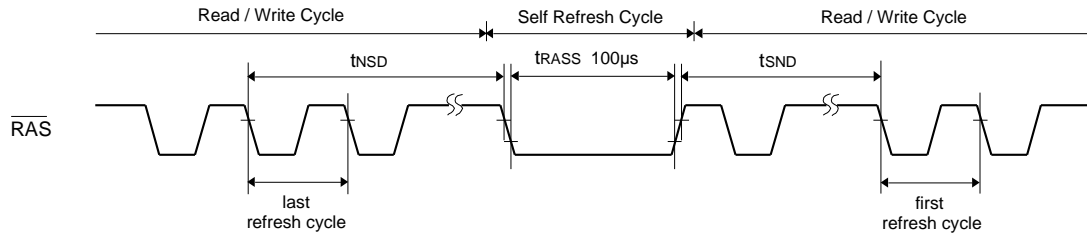
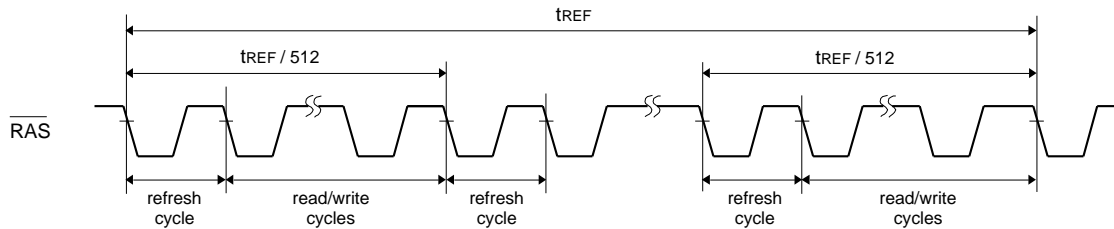


Table 2

Read / Write Cycle	Read / Write → Self Refresh	Self Refresh → Read / Write
CBR distributed refresh	t_{NSD} 250µs	t_{NSD} 250µs
RAS only distributed refresh	t_{NSD} 16µs	t_{NSD} 16µs

(B) Definition of distributed refresh



Definition of CBR distributed refresh (Including extended refresh)

The CBR distributed refresh performs more than 512 constant period (250µs max.) CBR cycles within 128 ms.

Definition of \overline{RAS} only distributed refresh

All combinations of nine row address signals ($A_0 \sim A_8$) are selected during 512 constant period (16µs max.) \overline{RAS} only refresh cycles within 8.2 ms.

Note:

Hidden refresh may be used instead of CBR refresh.
RAS/CAS refresh may be used instead of \overline{RAS} only refresh.

1.1 CBR distributed refresh

- Switching from read/write operation to self refresh operation.
The time interval from the falling edge of \overline{RAS} signal in the last CBR refresh cycle during read/write operation period to the falling edge of \overline{RAS} signal at the start of self refresh operation should be set within t_{NSD} (shown in table 2).

- Switching from self refresh operation to read/write operation.
The time interval from the rising edge of \overline{RAS} signal at the end of self refresh operation to the falling edge of \overline{RAS} signal in the first CBR refresh cycle during read/write operation period should be set within t_{NSD} (shown in table 2).

1.2 \overline{RAS} only distributed refresh

- Switching from read/write operation to self refresh operation.
The time interval t_{NSD} from the falling edge of \overline{RAS} signal in the last \overline{RAS} only refresh cycle during read/write operation period to the falling edge of \overline{RAS} signal at the start of self refresh operation should be set within 16µs.
- Switching from self refresh operation to read/write operation.
The time interval t_{NSD} from the rising edge of \overline{RAS} signal at the end of self refresh operation to the falling edge of \overline{RAS} signal in the first CBR refresh cycle during read/write operation period should be set within 16µs.

FAST PAGE MODE 4194304-BIT (262144-WORD BY 16-BIT) DYNAMIC RAM

2. Burst refresh during Read/Write operation

(A) Timing diagram

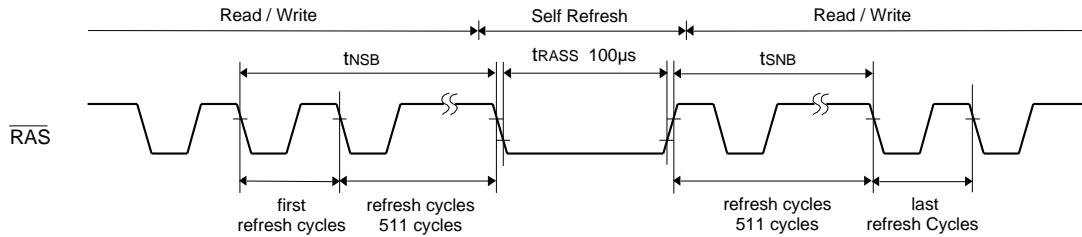
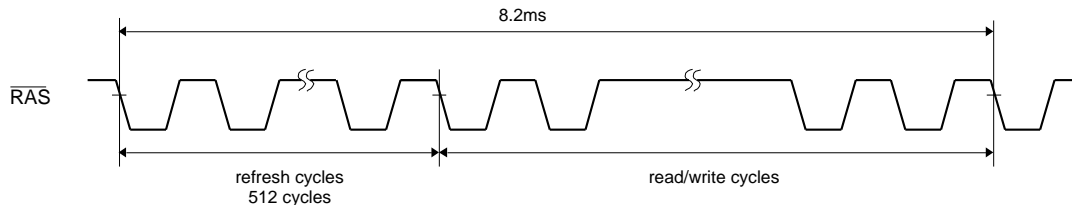


Table 3

Read / Write Cycle	Read / Write → Self Refresh	Self Refresh → Read / Write
CBR burst refresh	$t_{NSB} \ 8.2ms$	$t_{NSB} \ 8.2ms$
RAS only burst refresh	$t_{NSB}+t_{SNB} \ 8.2ms$	

(B) Definition of burst refresh



Definition of CBR burst refresh

The CBR burst refresh performs more than 512 continuous CBR cycles within 8.2 ms.

Definition of RAS only burst refresh

All combination of nine row address signals (A_0-A_8) are selected during 512 continuous RAS only refresh cycles within 8.2 ms.

2.1 CBR burst refresh

- Switching from read/write operation to self refresh operation. The time interval t_{NSB} from the falling edge of RAS signal in the first CBR refresh cycle during read/write operation period to the falling edge of RAS signal at the start of self refresh operation should be set within 8.2 ms.
- Switching from self refresh operation to read/write operation. The time interval t_{SNB} from the rising edge of RAS signal at the end of self refresh operation to the falling edge of RAS signal in the last CBR refresh cycle during read/write operation period should be set within 8.2 ms.

2.2 RAS only burst refresh

- Switching from read/write operation to self refresh operation. The time interval from the falling edge of RAS signal in the first RAS only refresh cycle during read/write operation period to the falling edge of RAS signal at the start of self refresh operation should be set within t_{NSB} (shown in table 3).
- Switching from self refresh operation to read/write operation. The time interval from the rising edge of RAS signal at the end of self refresh operation to the falling edge of RAS signal in the last RAS only refresh cycle during read/write operation period should be set within t_{SNB} (shown in table 3).